(12) INTERNATIONAL APPLICATION PUBLISHED UNDER THE PATENT COOPERATION TREATY (PCT)

(19) World Intellectual Property Organization
International Bureau

(43) International Publication Date
8 October 2009 (08.10.2009)

PCT

(10) International Publication Number
WO 2009/122275 A1

(51) International Patent Classification:
G03F 7/00 (2006.01) *G03F 7/40* (2006.01)

(21) International Application Number:
PCT/IB2009/005170

(22) International Filing Date:
30 March 2009 (30.03.2009)

(25) Filing Language: English

(26) Publication Language: English

(30) Priority Data:
12/061,061 2 April 2008 (02.04.2008) US

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(81) Designated States *(unless otherwise indicated, for every kind of national protection available)*: AE, AG, AL, AM, AO, AT, AU, AZ, BA, BB, BG, BH, BR, BW, BY, BZ, CA, CH, CN, CO, CR, CU, CZ, DE, DK, DM, DO, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, GT, HN, HR, HU, ID, IL, IN, IS, JP, KE, KG, KM, KN, KP, KR, KZ, LA, LC, LK, LR, LS, LT, LU, LY, MA, MD, ME, MG, MK, MN, MW, MX, MY, MZ, NA, NG, NI, NO, NZ, OM, PG, PH, PL, PT, RO, RS, RU, SC, SD, SE, SG, SK, SL, SM, ST, SV, SY, TJ, TM, TN, TR, TT, TZ, UA, UG, UZ, VC, VN, ZA, ZM, ZW.

(84) Designated States *(unless otherwise indicated, for every kind of regional protection available)*: ARIPO (BW, GH, GM, KE, LS, MW, MZ, NA, SD, SL, SZ, TZ, UG, ZM, ZW), Eurasian (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM), European (AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HR, HU, IE, IS, IT, LT, LU, LV, MC, MK, MT, NL, NO, PL, PT, RO, SE, SI, SK, TR), OAPI (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG).

Published:

— *with international search report (Art. 21(3))*

— *before the expiration of the time limit for amending the claims and to be republished in the event of receipt of amendments (Rule 48.2(h))*

WO 2009/122275 A1

(54) Title: A PHOTORESIST IMAGE-FORMING PROCESS USING DOUBLE PATTERNING

(57) Abstract: A process for forming a photoresist pattern on a device, comprising; a) forming a layer of first photoresist on a substrate from a first photoresist composition; b) imagewise exposing the first photoresist; c) developing the first photoresist to form a first photoresist pattern; d) treating the first photoresist pattern with a hardening compound comprising at least 2 amino (NH2) groups, thereby forming a hardened first photoresist pattern; e) forming a second photoresist layer on the region of the substrate including the hardened first photoresist pattern from a second photoresist composition; f) imagewise exposing the second photoresist; and, g) developing the imagewise exposed second photoresist to form a second photoresist pattern between the first photoresist pattern, thereby providing a double photoresist pattern.